

Preferred Device

JFET Transistor

N-Channel

Features

• Pb-Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	25	Vdc
Gate-Source Voltage	V _{GS}	25	Vdc
Gate Current	IG	10	mAdc

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

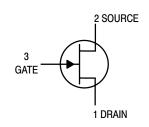
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.



ON Semiconductor®

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SOT-23 (TO-236AB) CASE 318-08 STYLE 10

MARKING DIAGRAM



6C = Specific Device Code

M = Date Code

= Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBFU310LT1	SOT-23	3000 Tape & Reel
MMBFU310LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

MMBFU310LT1

TA = 25°C unless otherwise noted)

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Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate–Source Breakdown Voltage – (I _G = –1.0 μAdc, V _{DS} = 0)	$V_{DS} = 0$ $V_{(BR)GSS}$		_	Vdc
Gate 1 Leakage Current – (V _{GS} = –15 Vdc, V _{DS} = 0)		_	-150	рА
Gate 2 Leakage Current – (V _{GS} = –15 Vdc, V _{DS} = 0, T _A = 125°C)	I _{G2SS}	_	-150	nAdc
Gate Source Cutoff Voltage – (V _{DS} = 10 Vdc, I _D = 1.0 nAdc)	V _{GS(off)}	-2.5	-6.0	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain Current - (V _{DS} = 10 Vdc, V _{GS} = 0)	I _{DSS}	24	60	mAdc
Gate–Source Forward Voltage – (I _G = 10 mAdc, V _{DS} = 0)	V _{GS(f)}	_	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance – (V _{DS} = 10 Vdc, I _D = 10 mAdc, f = 1.0 kHz)	Y _{fs}	10	18	mmhos
Output Admittance – (V _{DS} = 10 Vdc, I _D = 10 mAdc, f = 1.0 kHz)	lyosl	-	250	μmhos
Input Capacitance – (V _{GS} = –10 Vdc, V _{DS} = 0 Vdc, f = 1.0 MHz)	C _{iss}	-	5.0	pF
Reverse Transfer Capacitance – (V _{GS} = –10 Vdc, V _{DS} = 0 Vdc, f = 1.0 MHz)	C _{rss}	-	2.5	pF

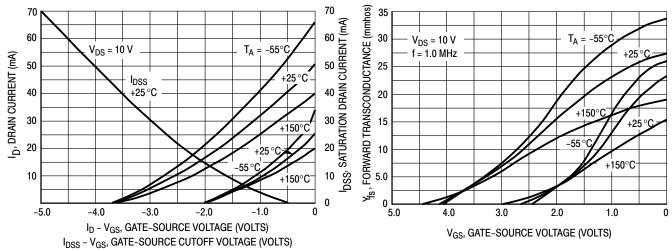


Figure 1. Drain Current and Transfer Characteristics vs Gate-Source Voltage

Figure 2. Forward Transconductance vs Gate-Source Voltage

MMBFU310LT1

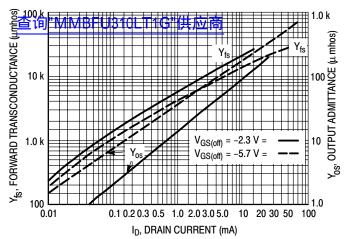


Figure 3. Common-Source Output Admittance and Forward Transconductance vs Drain Current

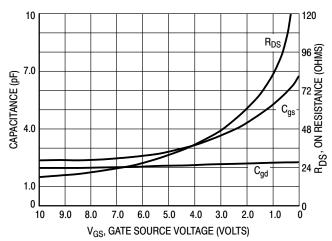


Figure 4. On Resistance and Junction Capacitance vs Gate-Source Voltage

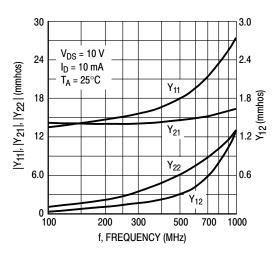


Figure 5. Common-Gate Y Parameter Magnitude vs Frequency

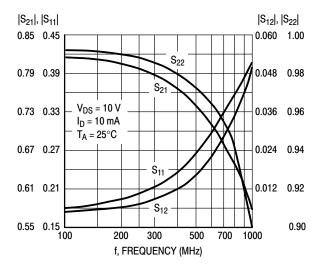


Figure 6. Common-Gate S Parameter Magnitude vs Frequency

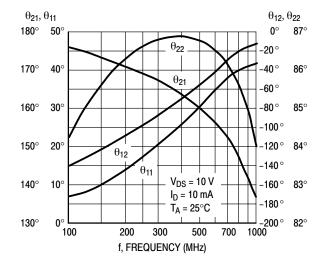


Figure 7. Common–Gate Y Parameter Phase–Angle vs Frequency

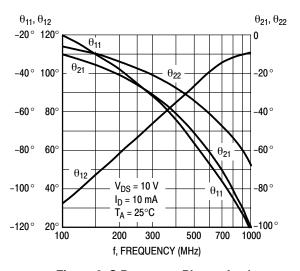


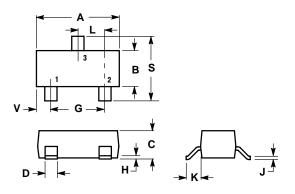
Figure 8. S Parameter Phase–Angle vs Frequency

MMBFU310LT1

查询"MMBFU310LT1G"供应商

PACKAGE DIMENSIONS

SOT-23 (TO-236AB) CASE 318-08 **ISSUE AH**



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF
- BASE MATERIAL. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

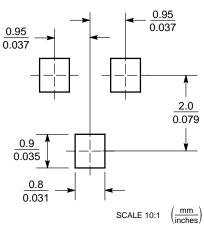
	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.1102	0.1197	2.80	3.04
В	0.0472	0.0551	1.20	1.40
С	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
Н	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

STYLE 10:

PIN 1. DRAIN 2. SOURCE

GATE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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